

09966689-092701

FIG. 1A

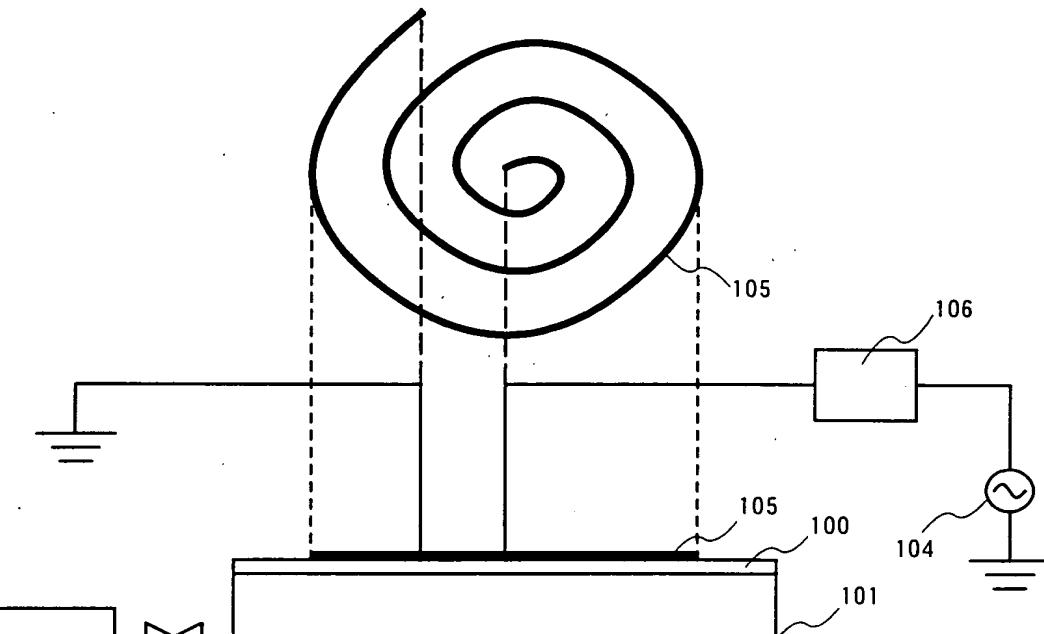


FIG. 1B

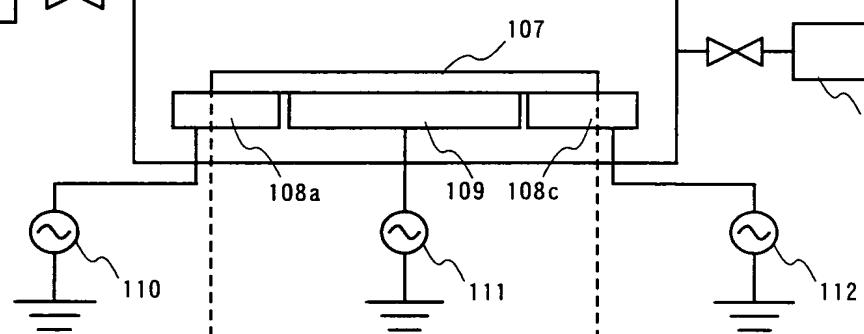
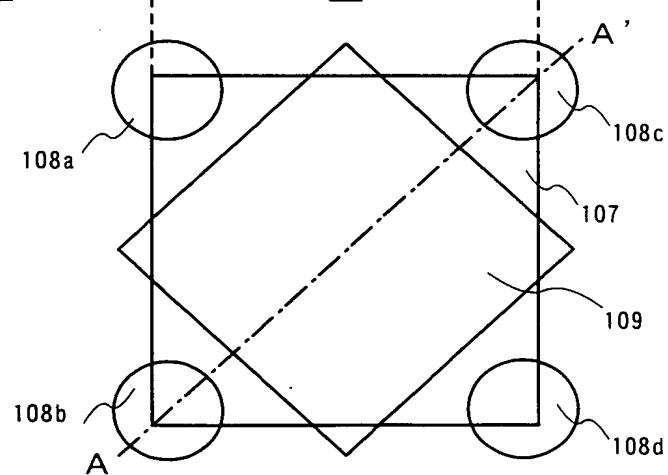


FIG. 1C



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FIG. 2A

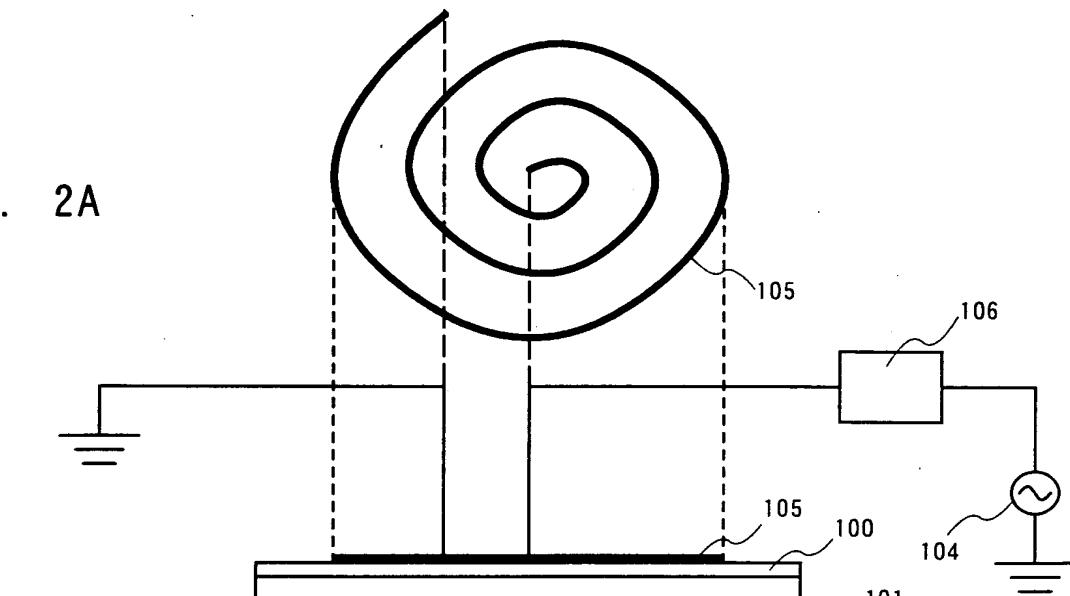


FIG. 2B

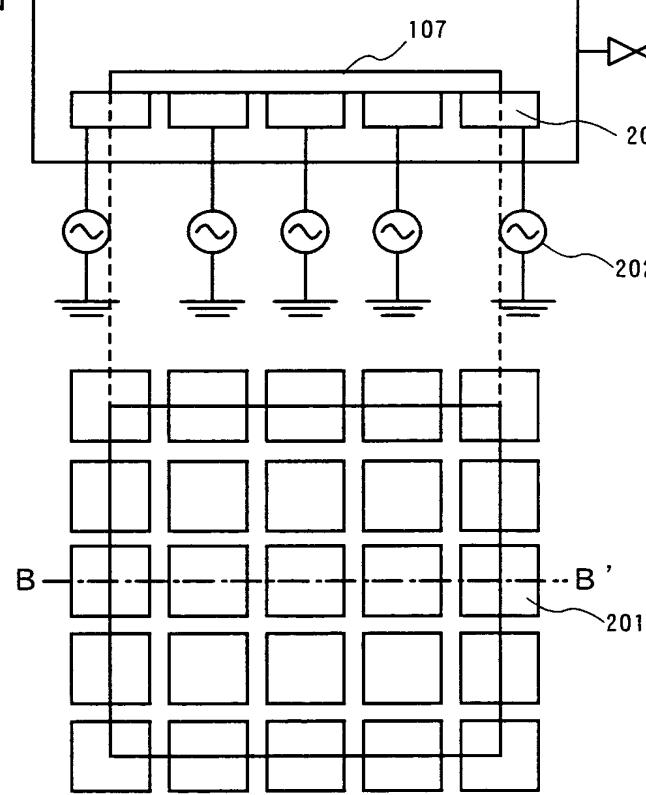


FIG. 2C

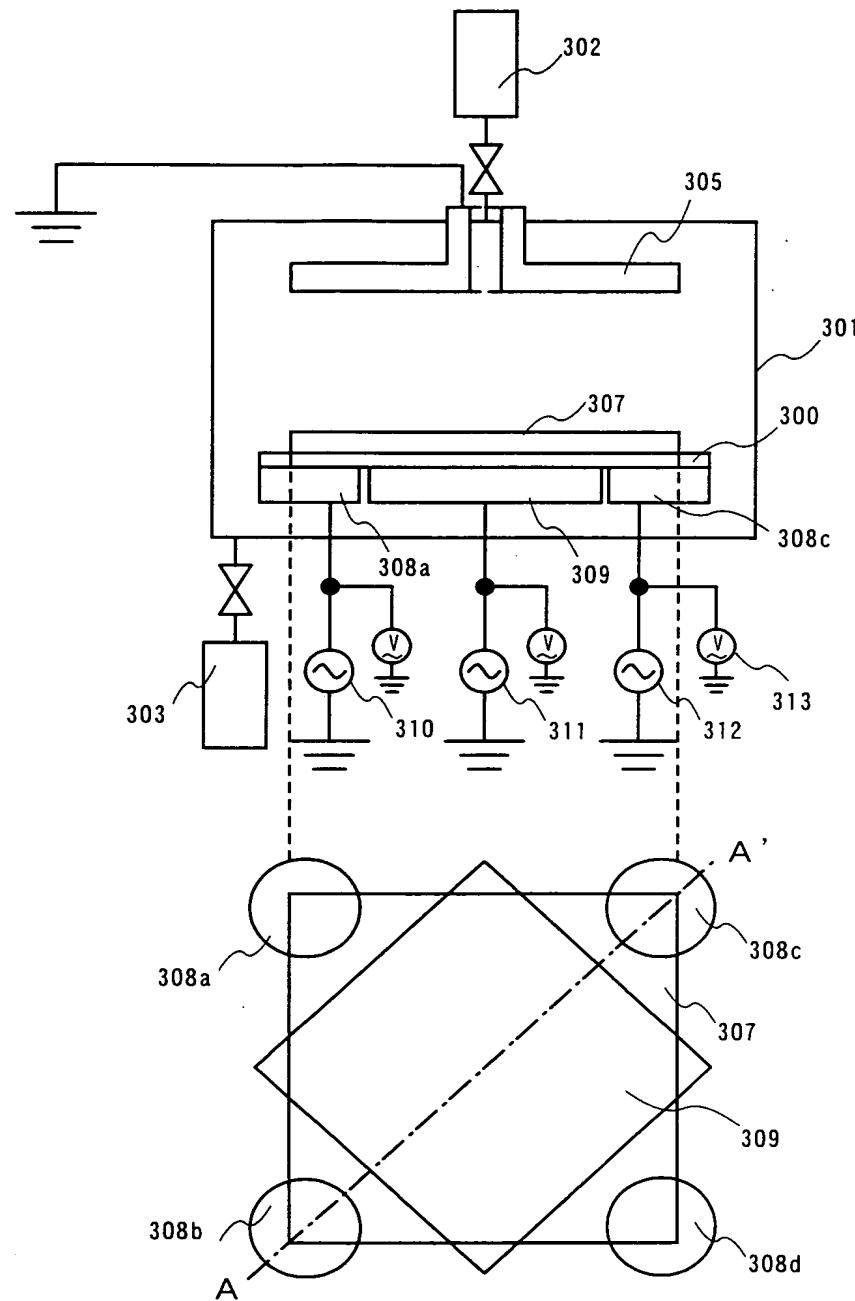


FIG. 3A

FIG. 3B

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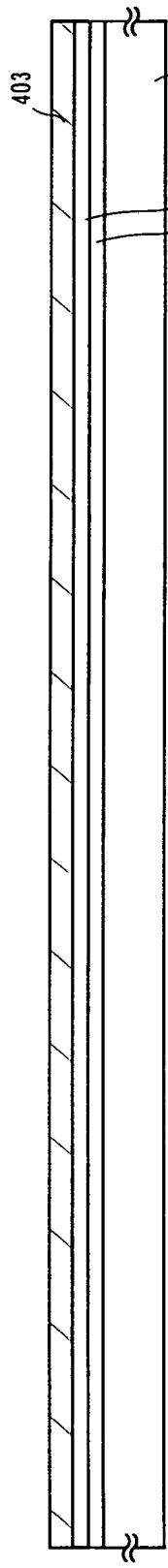


FIG. 4A



FIG. 4B

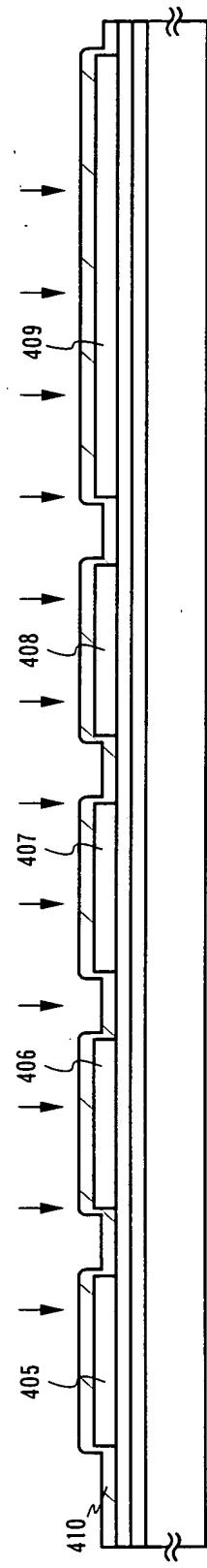


FIG. 4C

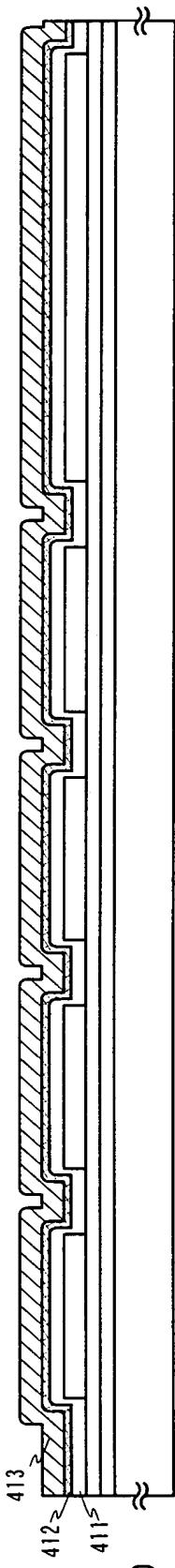


FIG. 4D

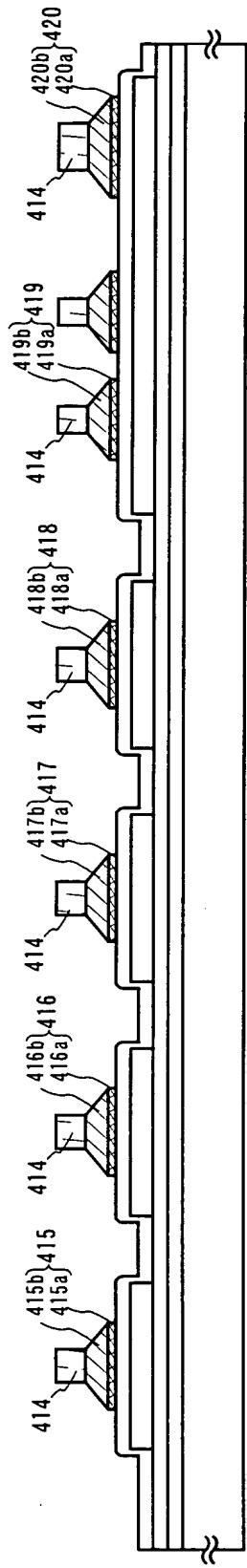


FIG. 5A

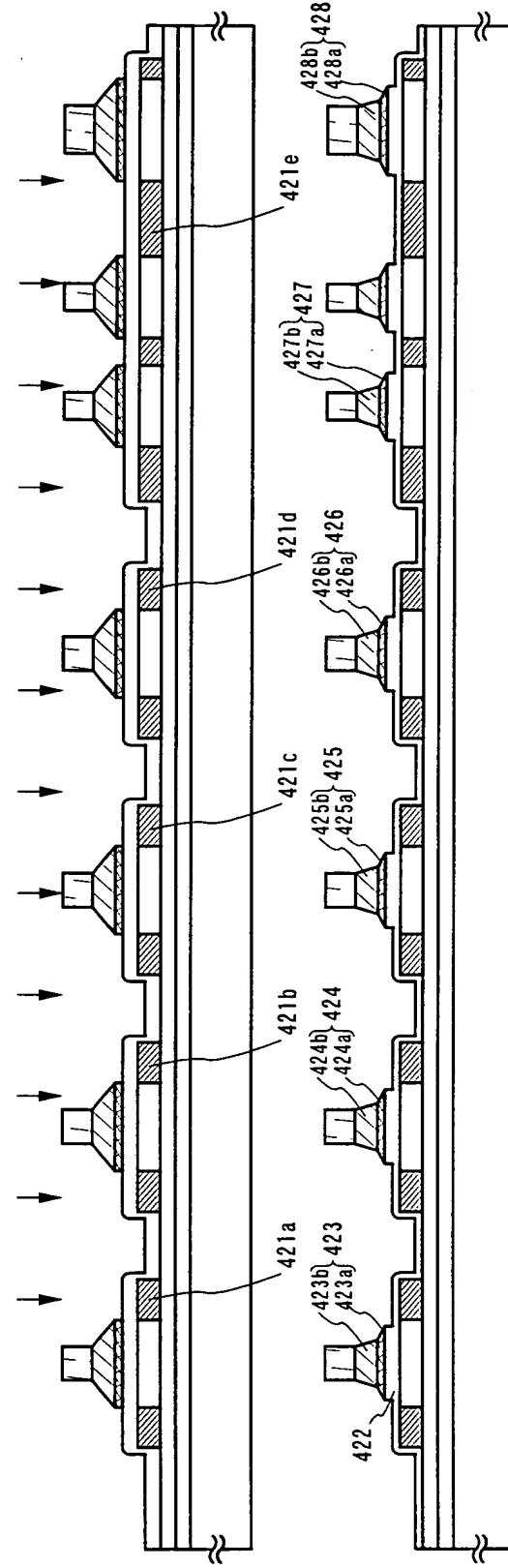


FIG. 5B

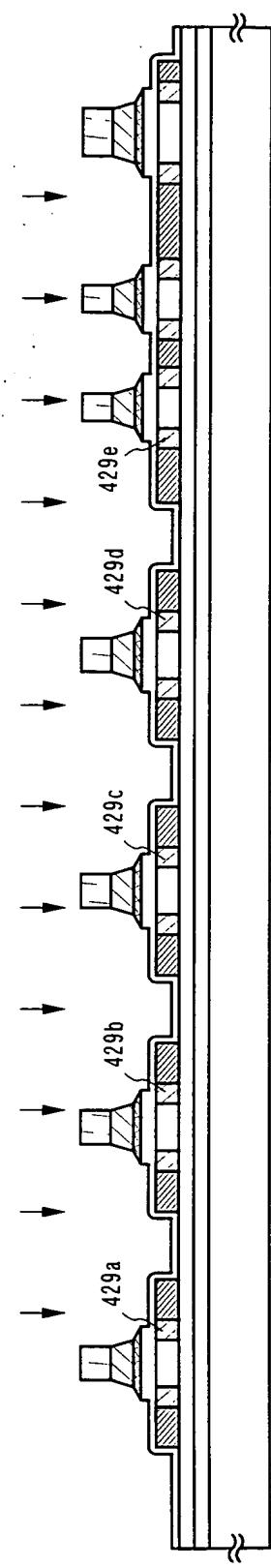


FIG. 5C

FIG. 5D

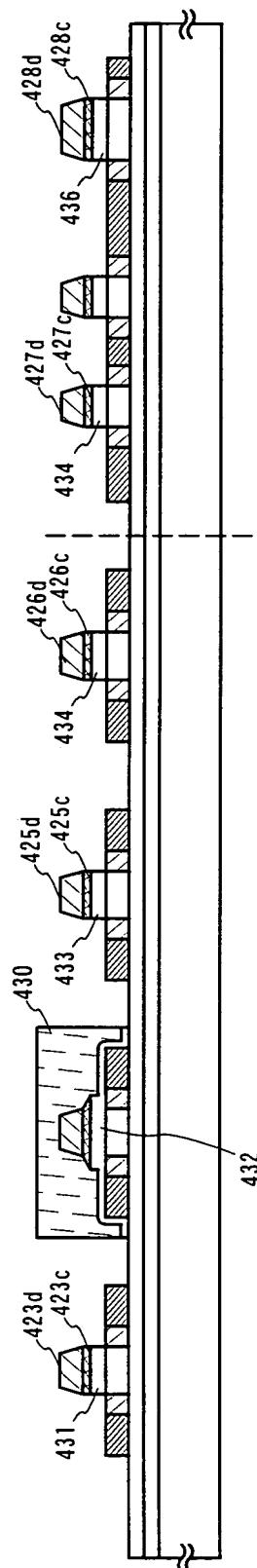
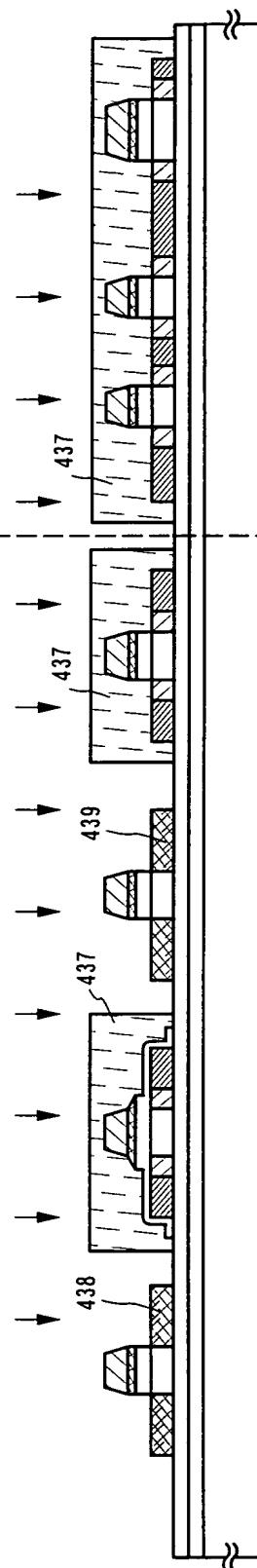


FIG. 6A



EIG 6B

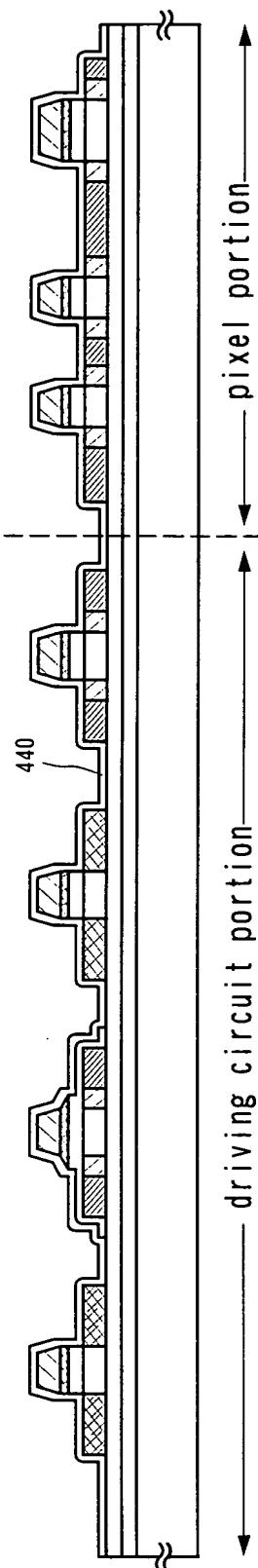


FIG. 6C

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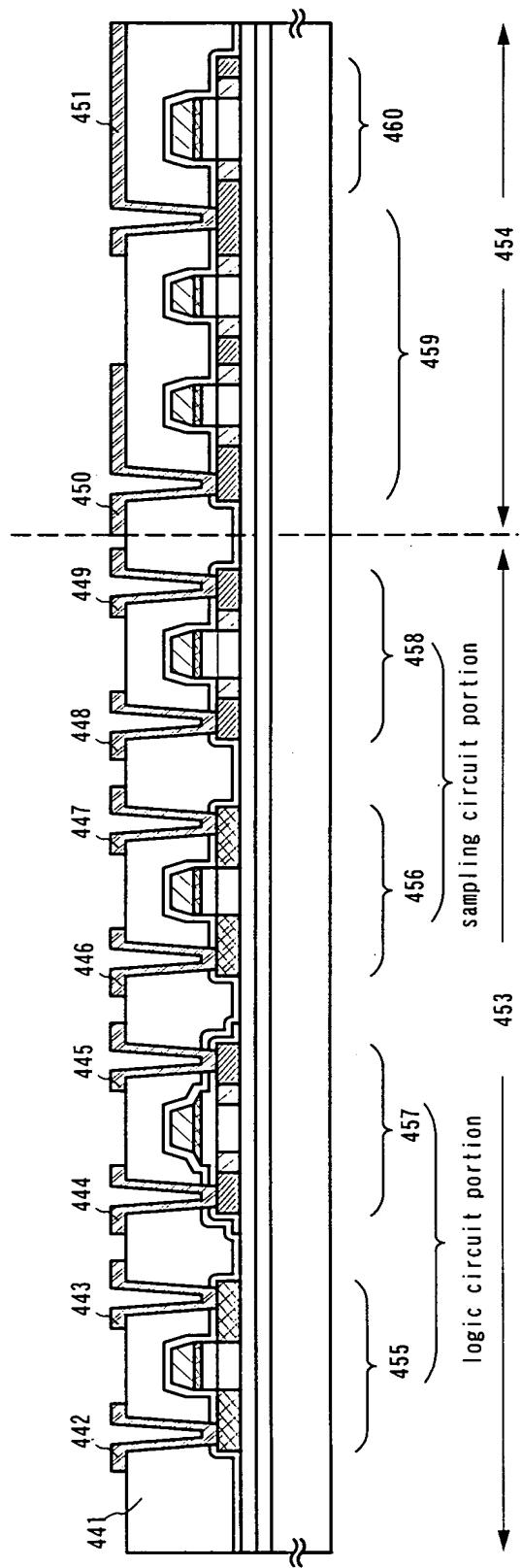


FIG. 7

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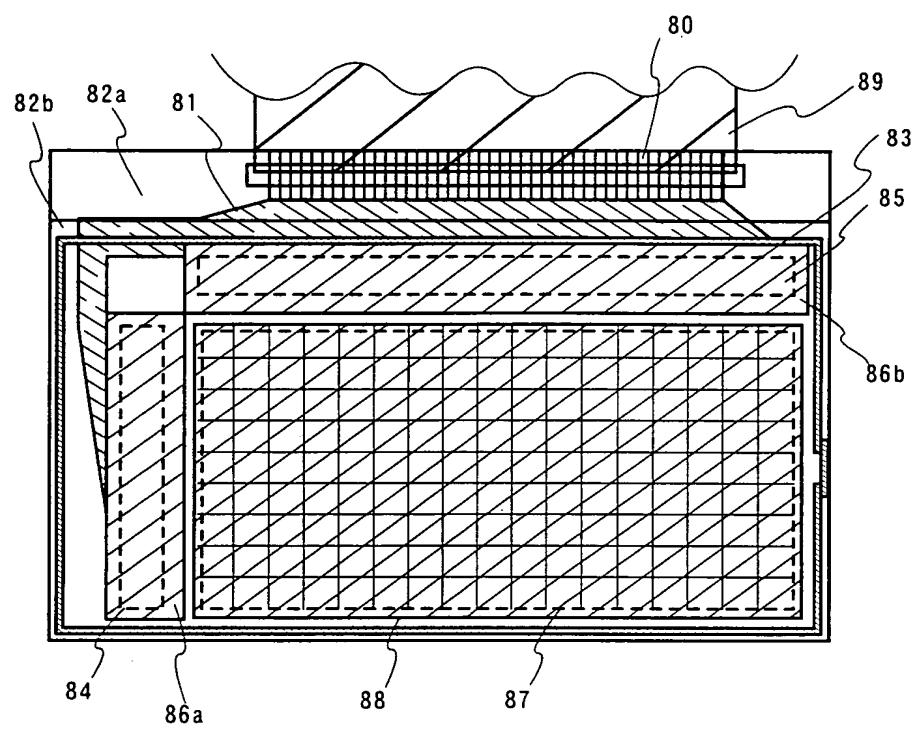


FIG. 8

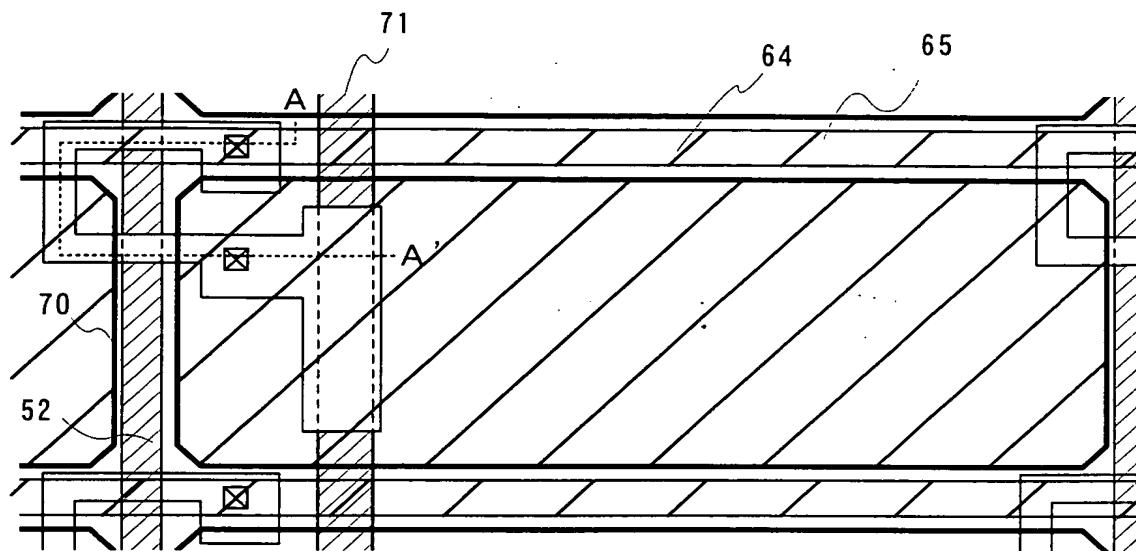


FIG. 9A

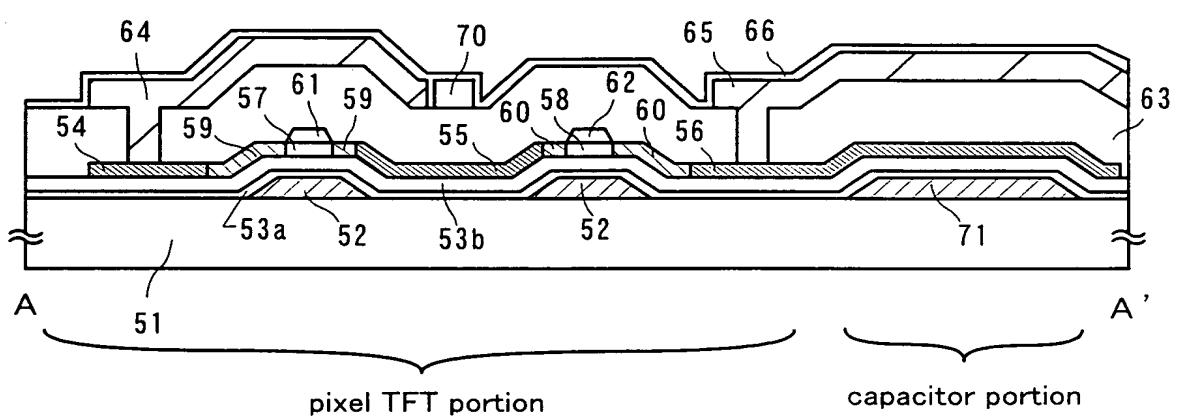


FIG. 9B

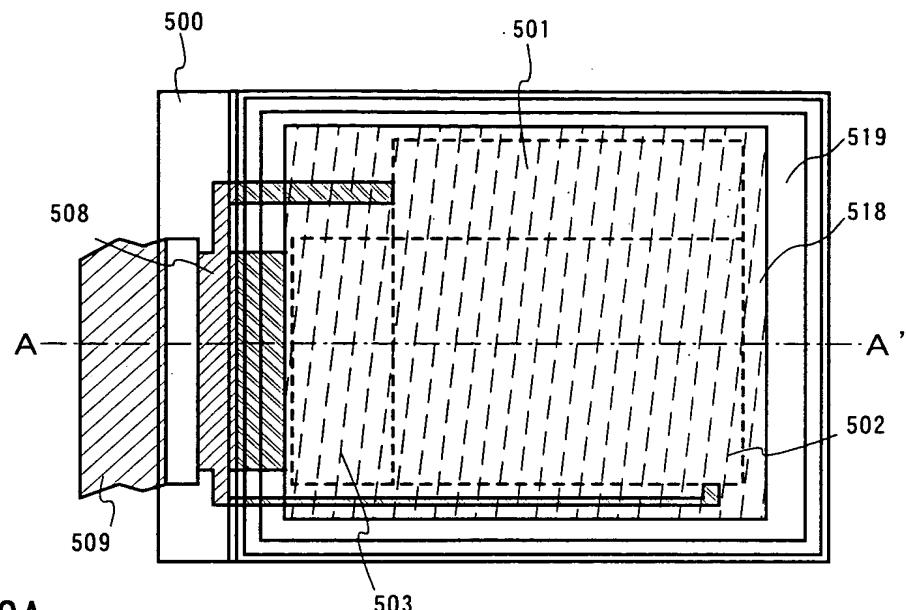


FIG. 10A

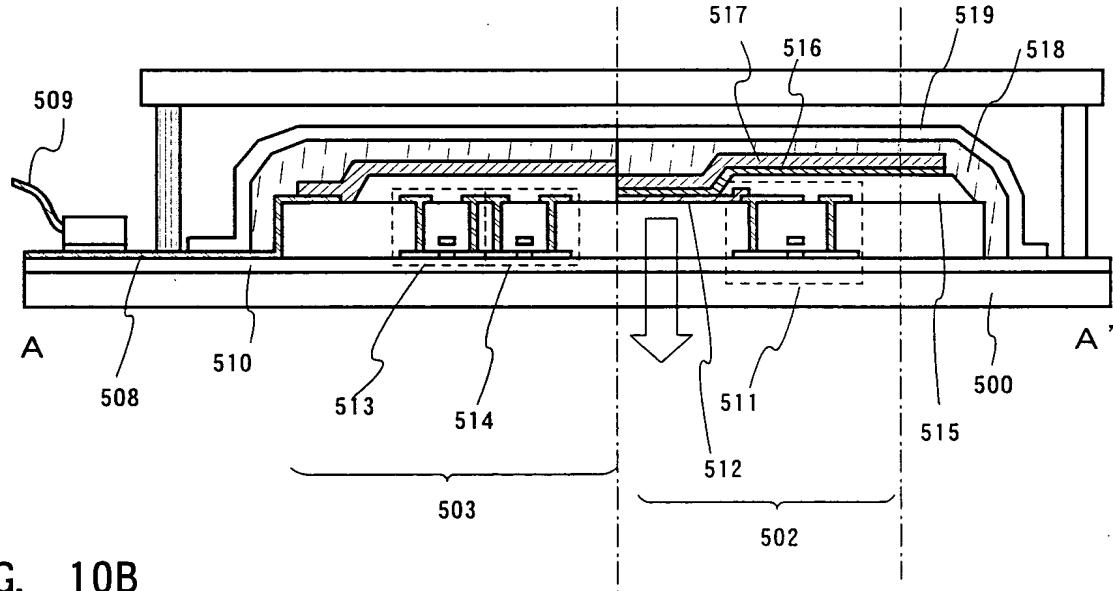


FIG. 10B

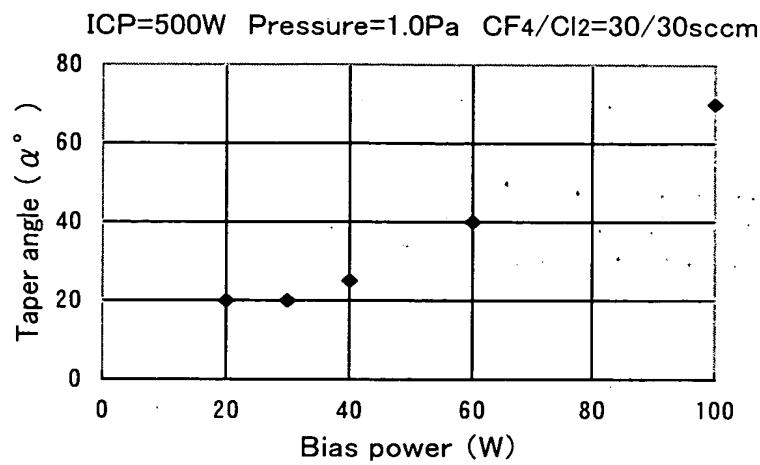


FIG. 11 Dependence of taper angle on bias power.

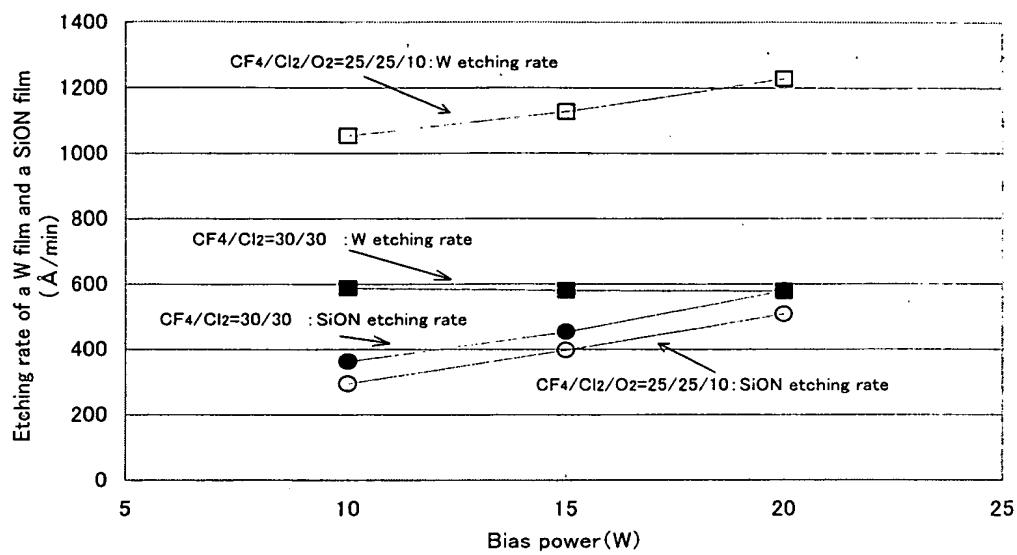


FIG. 12

Dependence of an etching rate of a W film and an SiON film on bias power.

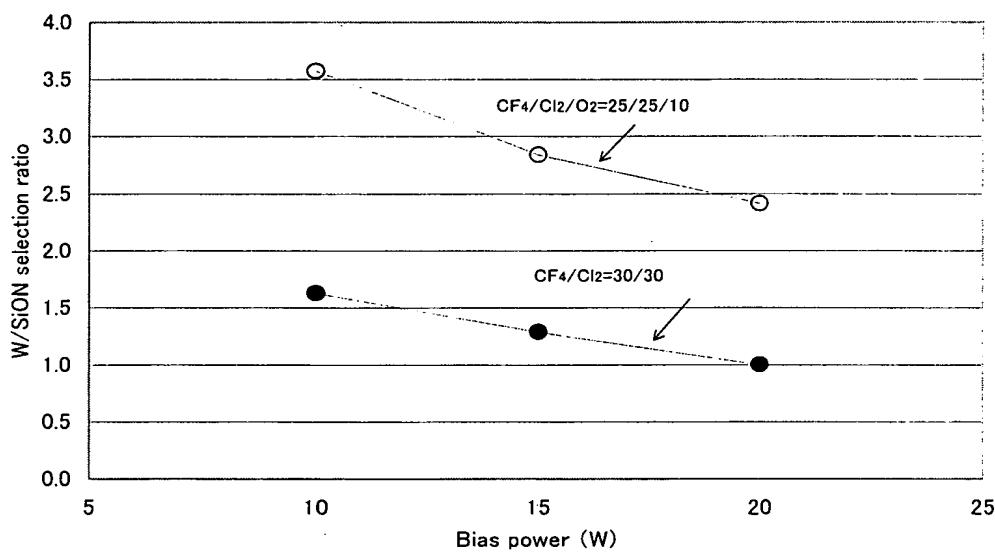


FIG. 13

Dependence of a selection ratio between a W film and an SiON film on a bias power.

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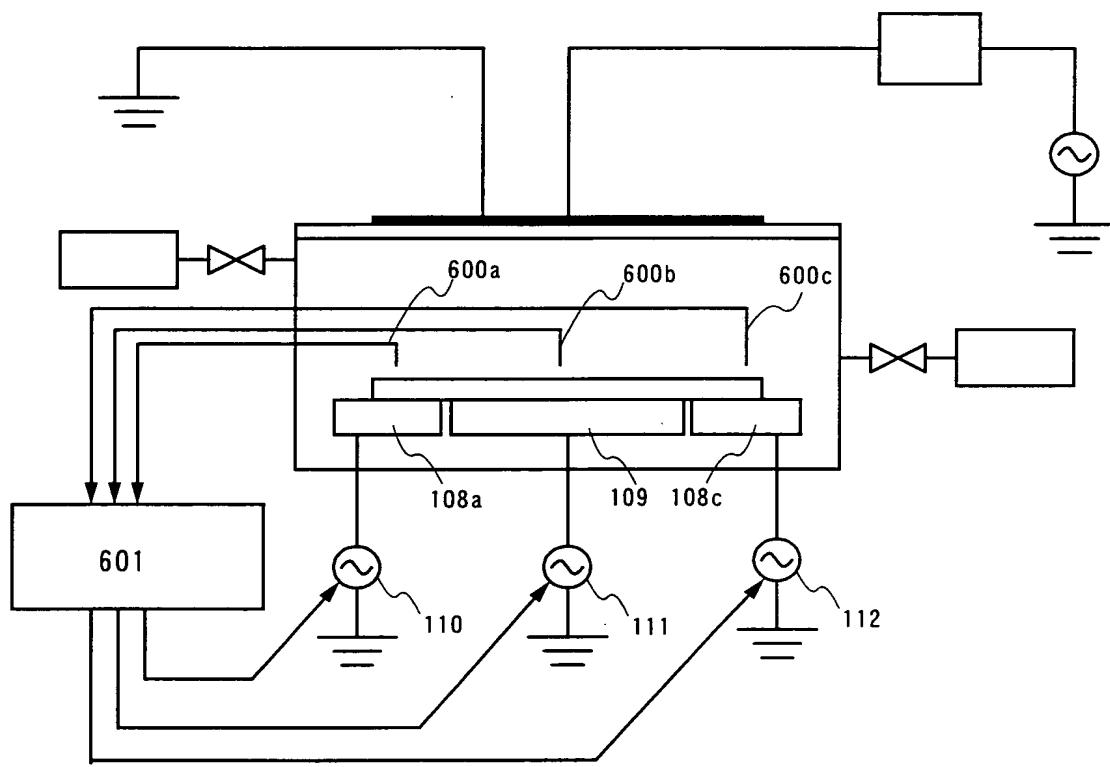
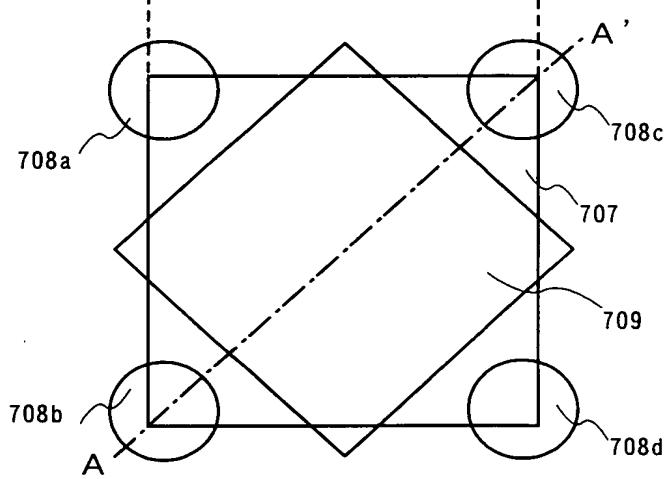
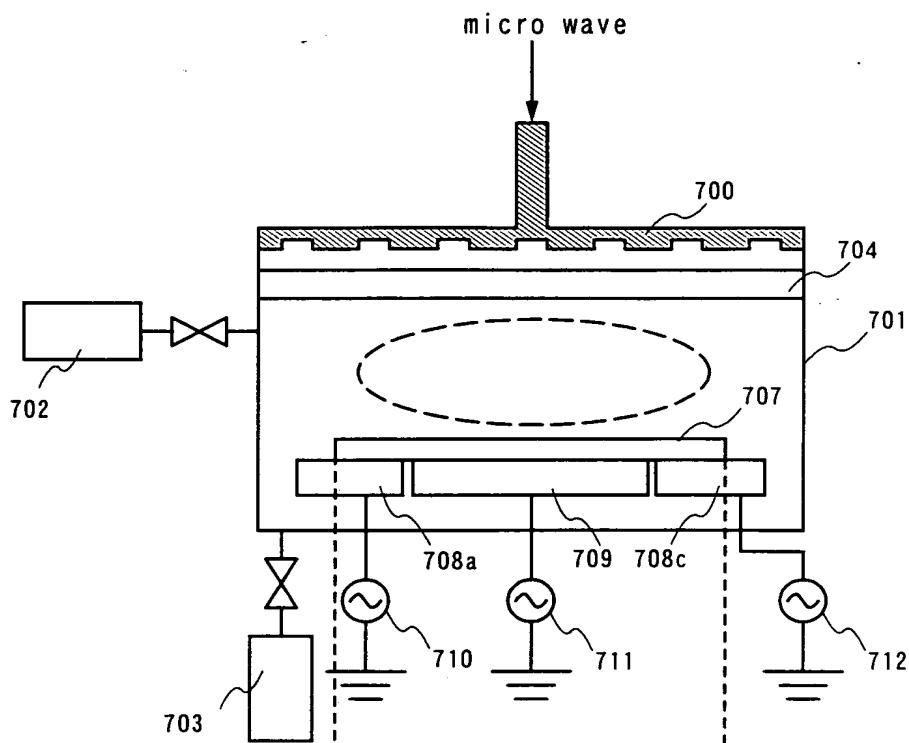


FIG. 14

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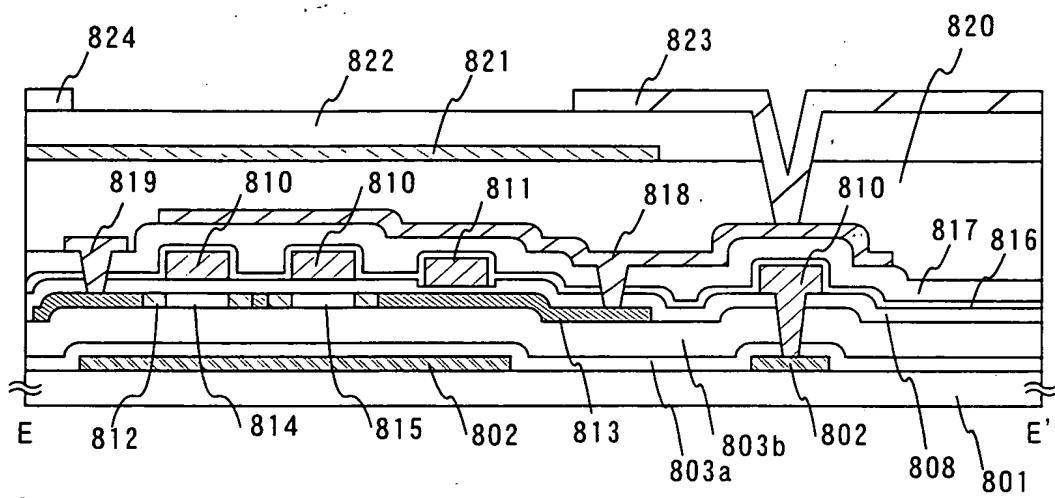


FIG. 16A

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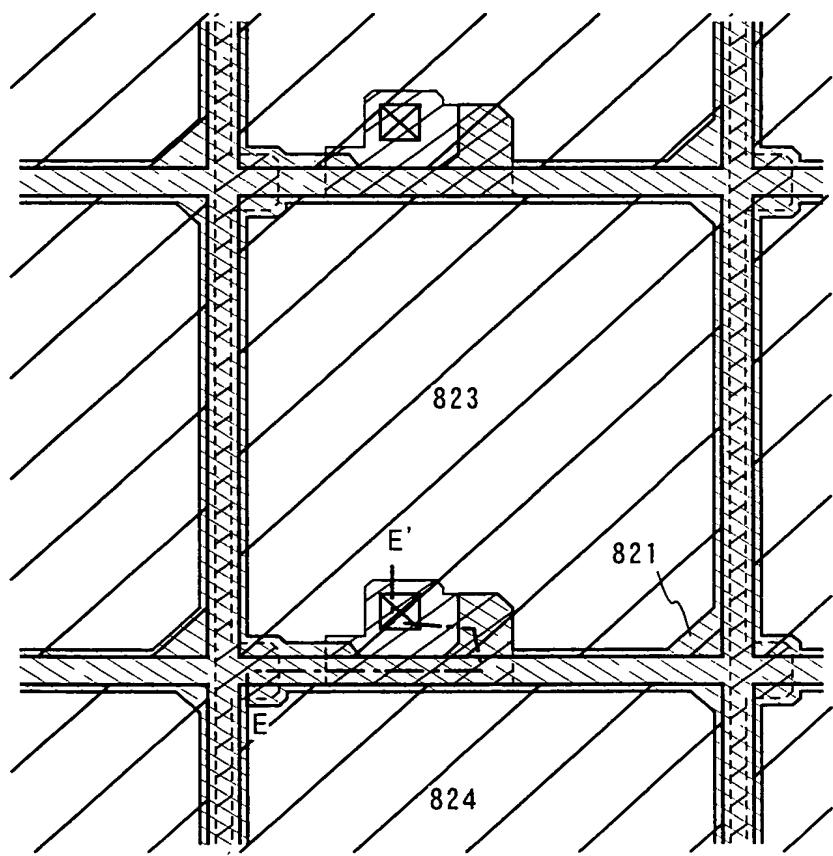


FIG. 16B

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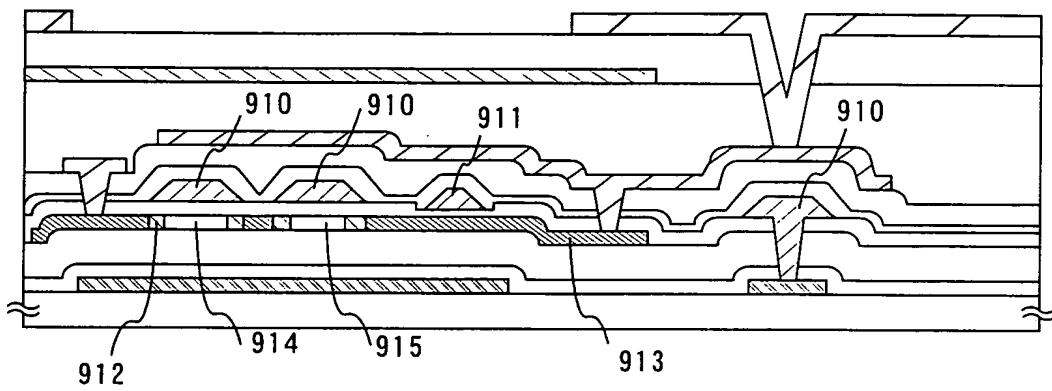


FIG. 17

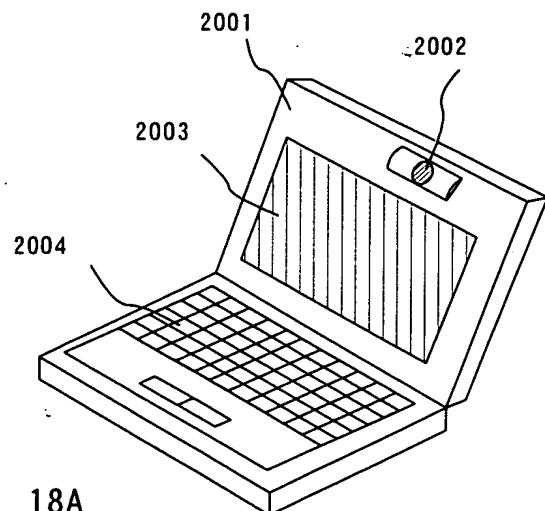


FIG. 18A

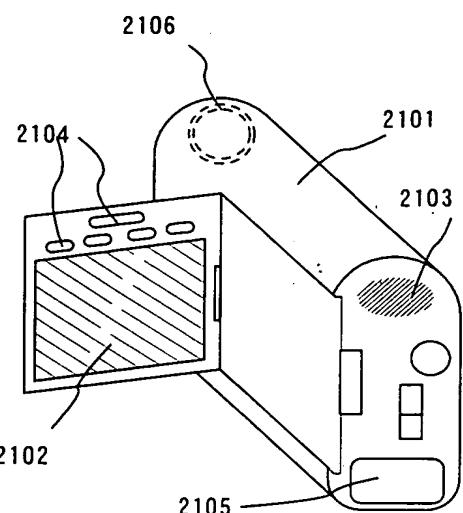


FIG. 18B

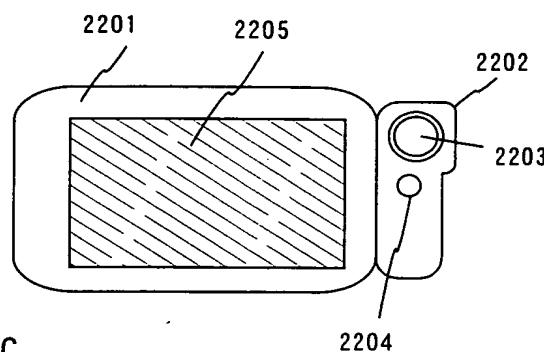


FIG. 18C

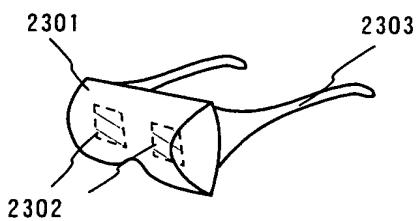


FIG. 18D

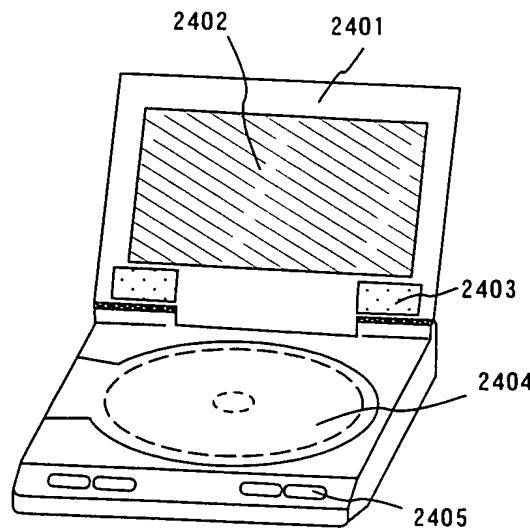


FIG. 18E

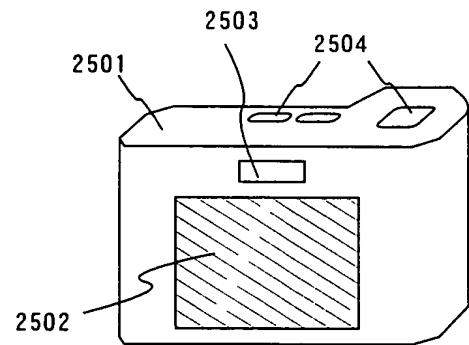


FIG. 18F

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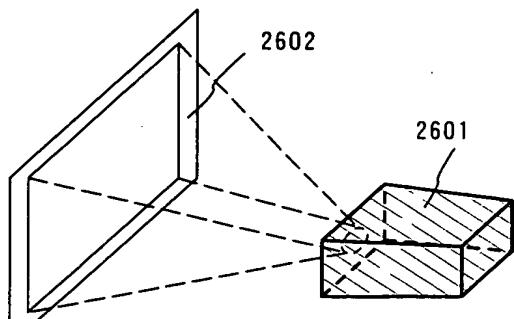


FIG. 19A

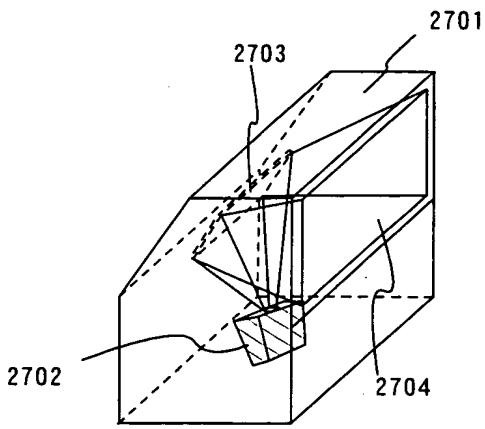


FIG. 19B

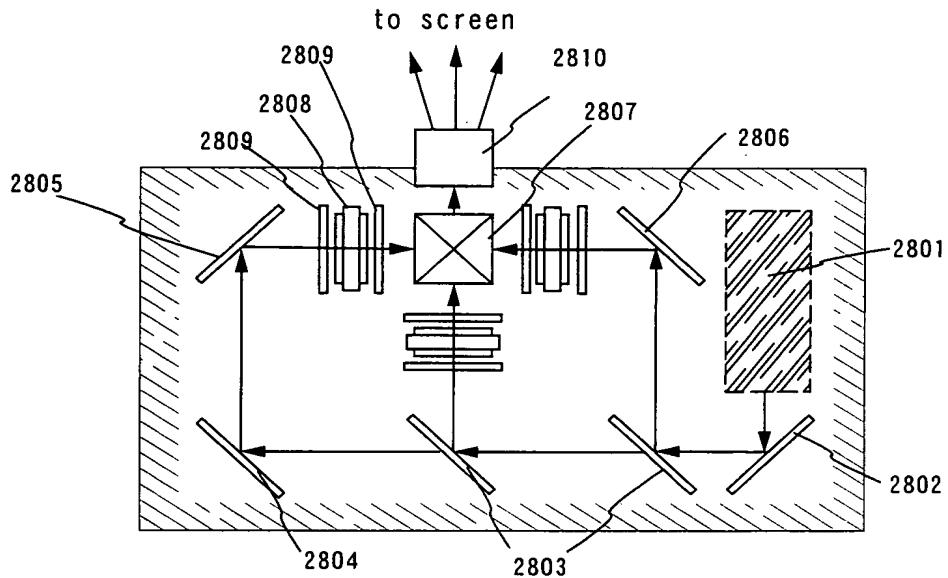


FIG. 19C

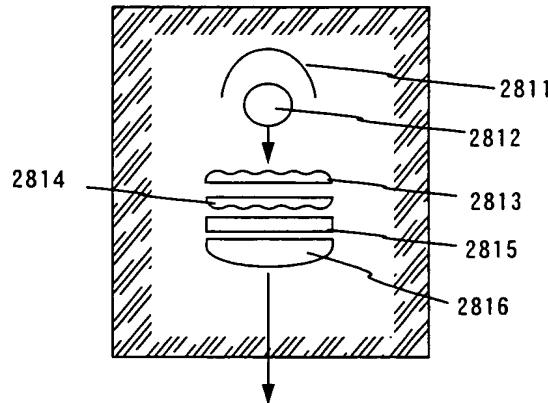


FIG. 19D

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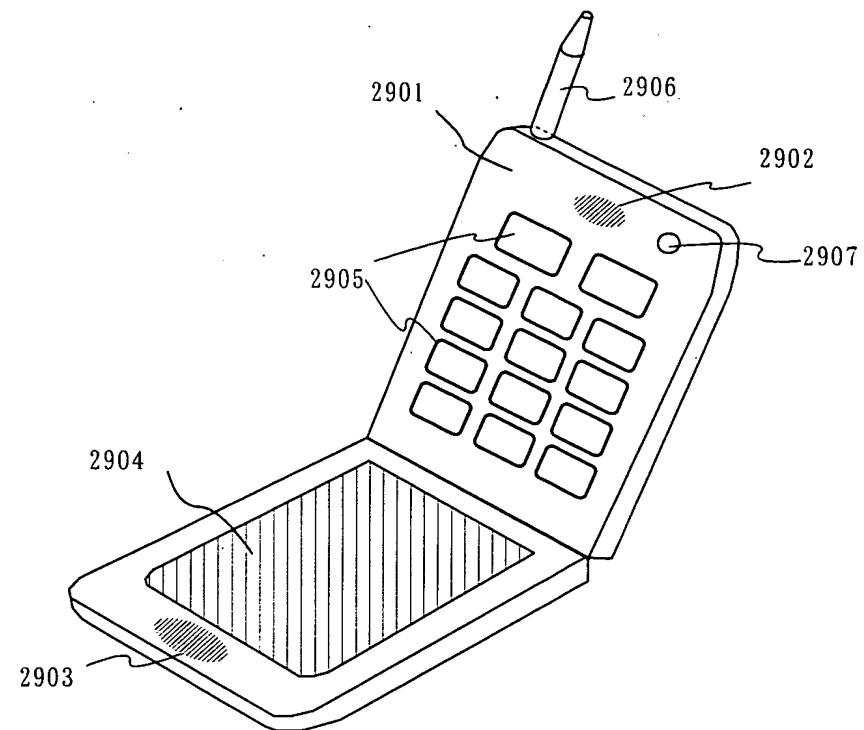


FIG. 20A

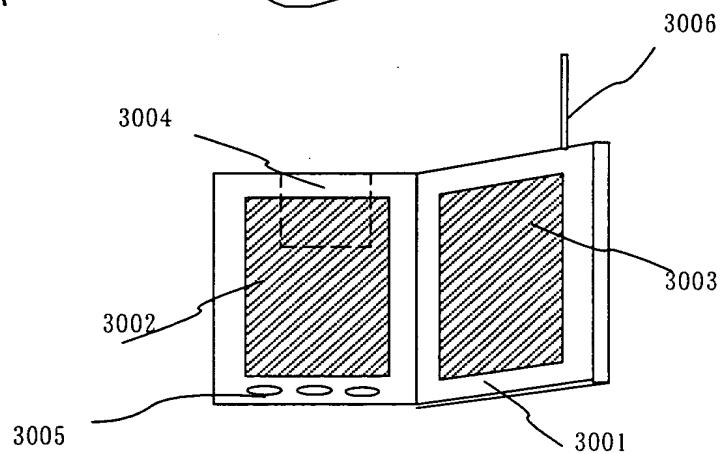


FIG. 20B

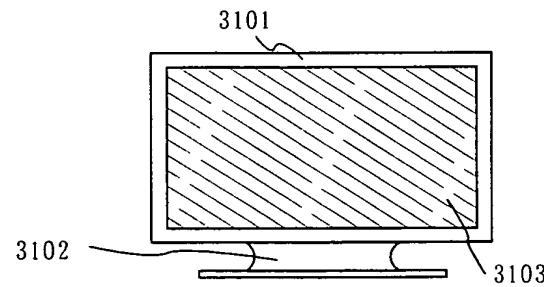


FIG. 20C

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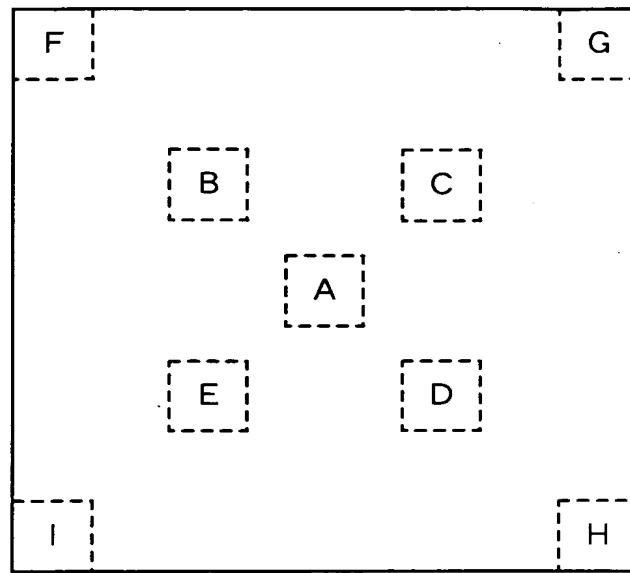


FIG. 21A

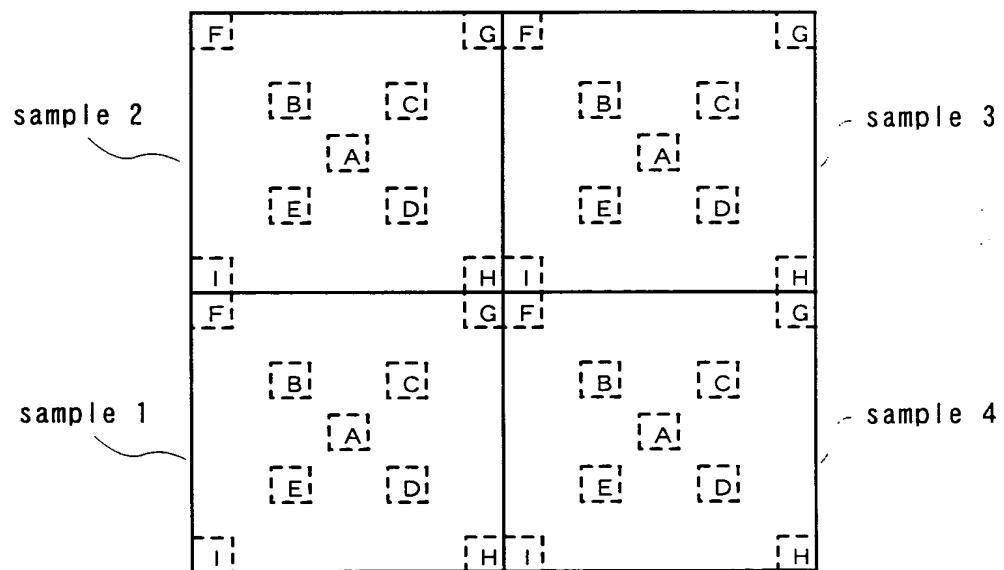


FIG. 21B